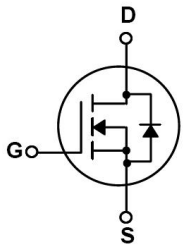
TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

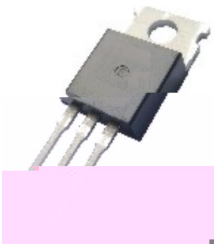
, , , , 100

Fast Switching, Low ON Resistance, Low Gate Charge, Low Reverse transfer capacitances,100% Single Pulse avalanche energy Test.

UPS

For UPS, inverters, lightin.





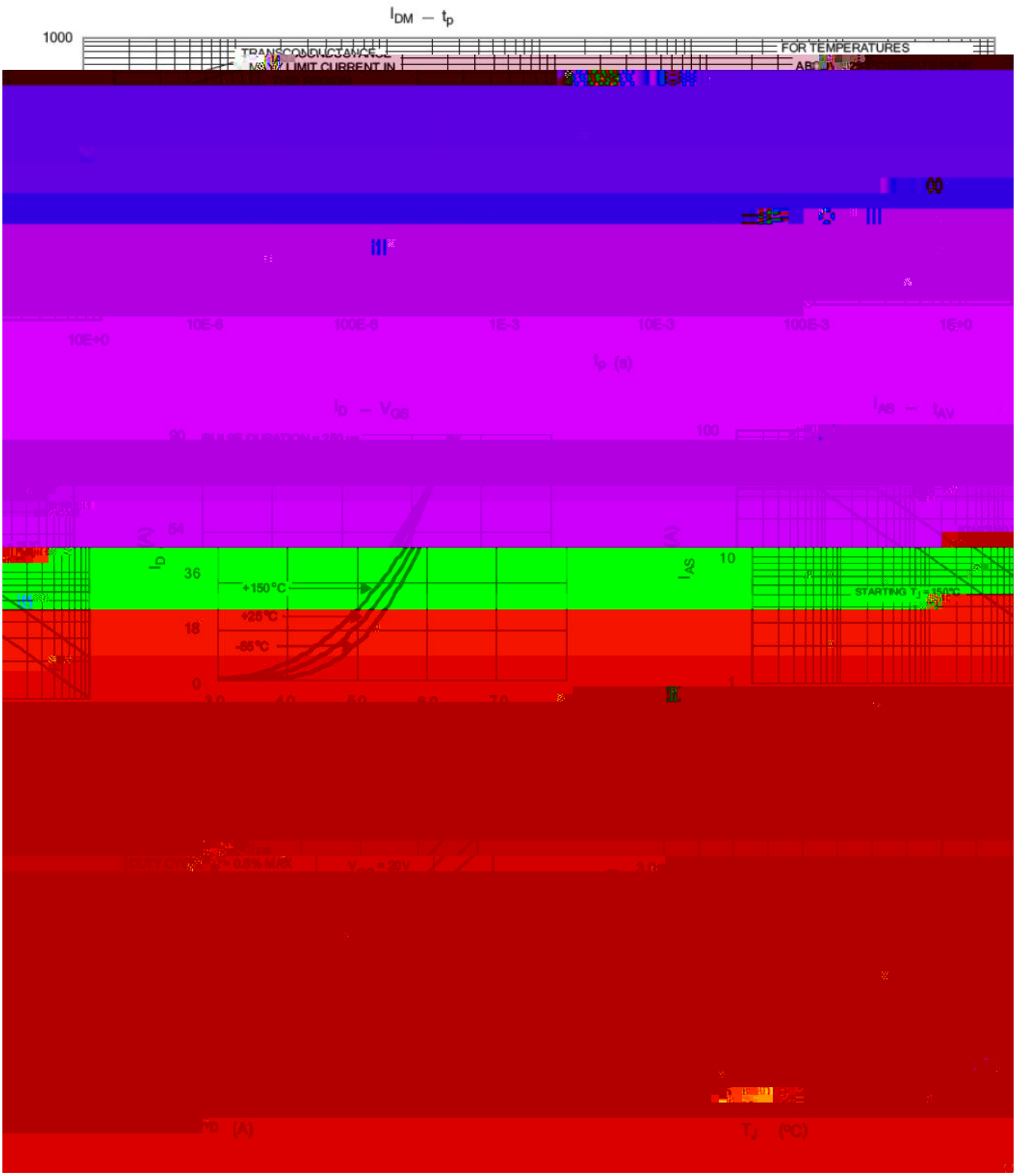
PIN1 G PIN 2 D PIN 3 S

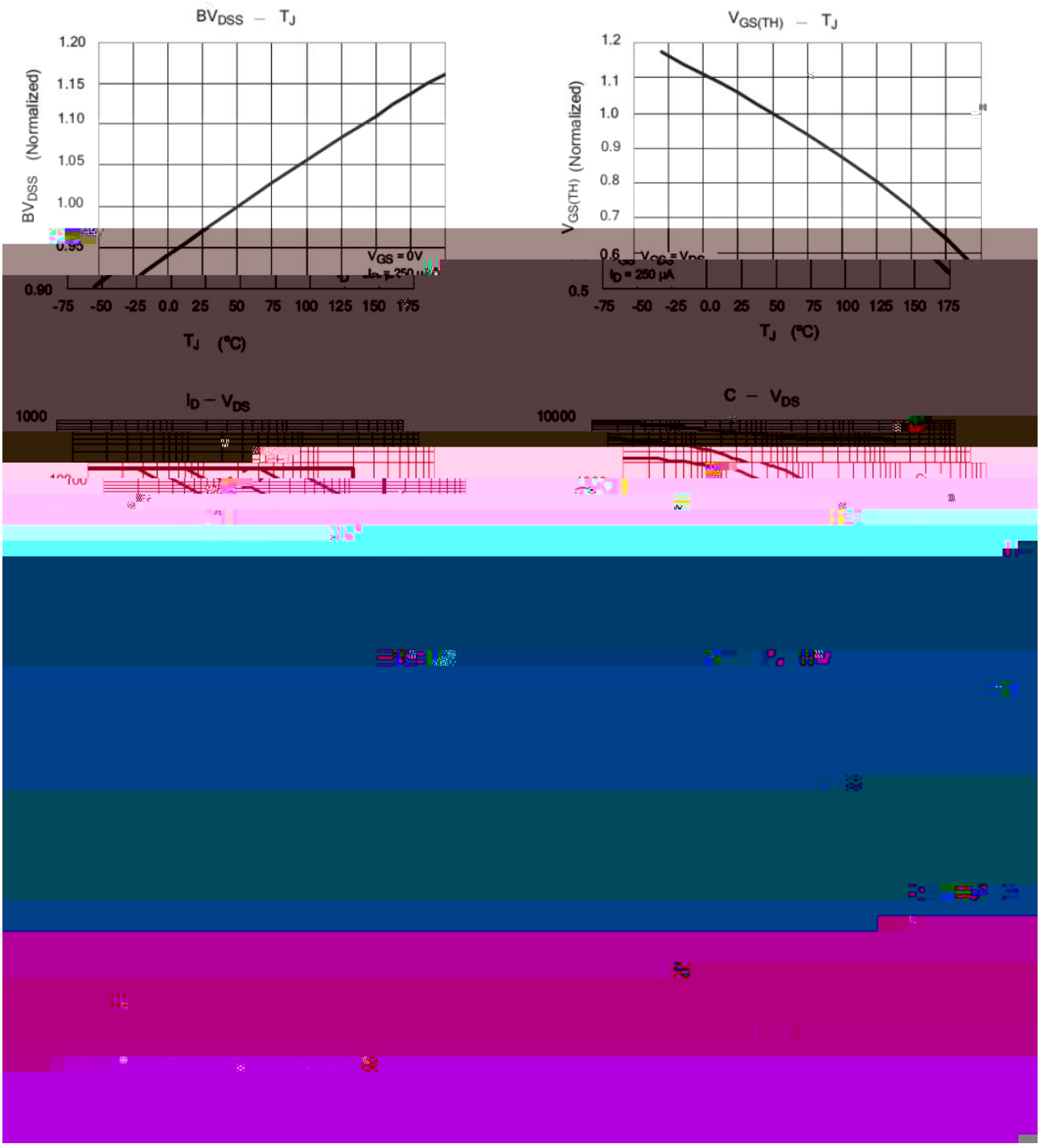
See Marking Instructions.

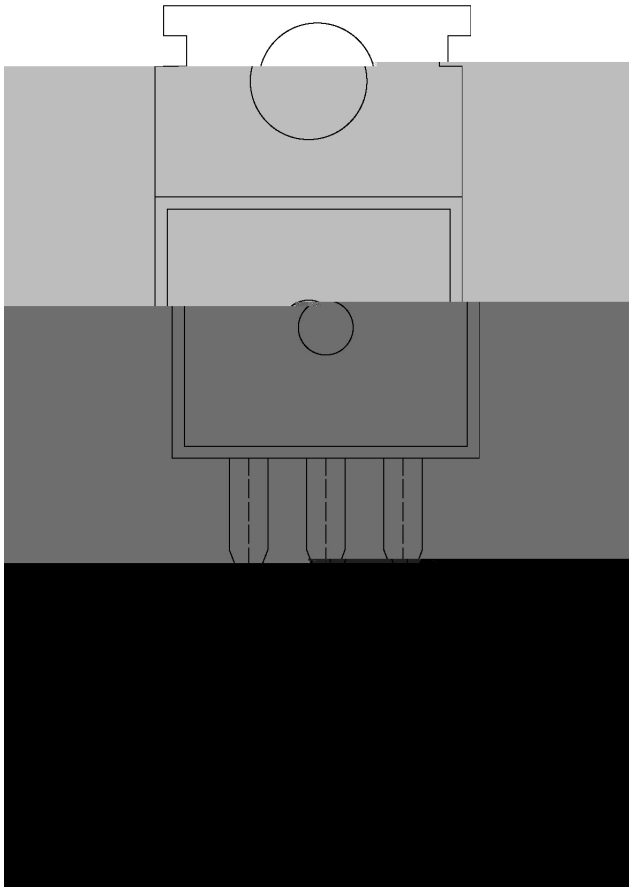
Total Gate Charge	Q_g	I_D=20A V_{DD}=100V V_{GS} = 10V		68		nC
Gate-Source Charge	Q_{gs}			17		
Gate-Drain Charge	Q_{gd}			16		
Continuous Source Current	I_S				40	A
Maximum Pulsed Current	I_{SM}				160	A
Diode Forward Voltage	V_{SD}	I_S=40A V_{GS}=0V			1.5	V
Reverse Recovery Time	t_{rr}	I_S=20A T_j=25 d_{IF}/d_t=100A/us,V_{GS}=0V		250		ns
Reverse Recovery Charge	Q_{rr}			1.5		μC

Notes:

a1 L=1.0mH, I_D=31.6A, Start T_J=25 a2 I_{SD} =10A,di/dt ≤100A/us,V_{DD}≤B_{VDS}, Start T_J=25


I_{DM} – t_p
1000
FOR TEMPERATURES
10E+0
10E-6
100E-6
1E-3
10E-3
100E-3
1E+0
t_p (s)
I_D – V_{GS}
I_{AS} – t_{AV}
100
36
18
0
+150 °C
+25 °C
-55 °C
10
STARTING T_J = 150°C
I_D (A)
T_J (°C)


BVDSS – TJ
BVDSS (Normalized)
1.20
1.15
1.10
1.05
1.00
0.95
0.90
VGS = 0V
ID = 250 μA
-75 -50 -25 0.0 25 50 75 100 125 150 175
TJ (°C)
VGS(TH) – TJ
VGS(TH) (Normalized)
1.2
1.1
1.0
0.9
0.8
0.7
0.6
0.5
VGS = VDS
ID = 250 μA
-75 -50 -25 0.0 25 50 75 100 125 150 175
TJ (°C)
ID – VDS
1000
C – VDS
10000





1	25	150	60	90sec;	Note: 1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ BULK

Package Type	Units					Dimension		(unit mm^3)

/ TUBE

Package Type	Units					Dimension		(unit mm^3)